



100V PNP MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

Features

- BV_{CEO} > -100V
- I_C = -5A High Continuous Collector Current
- I_{CM} = -10A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < -90mV @ -1A
- $R_{SAT} = 60m\Omega$ for a Low Equivalent On-Resistance
- hFE Specified Up to -10A for a High Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Application

- Motor Driving
- Line Switching
- High Side Switches
- Subscriber Line Interface Cards (SLIC)

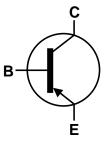
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.112 grams (Approximate)

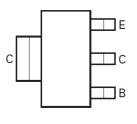




Top View



Device Symbol



Top View Pin-Out

May 2015

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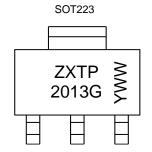
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP2013GTA	AEC-Q101	ZXTP2013	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information



ZXTP 2013G = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-140	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-5	Α
Peak Pulse Current	I _{CM}	-10	Α

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	P _D	3.0 24	W mW/°C
Power Dissipation (Note 6) Linear Derating Factor	P _D	1.6 12.8	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	42	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	78	°C/W
Thermal Resistance Junction to Lead (Note 7)	R _{θJL}	10.48	°C/W
Thermal Resistance Junction to Case (Note 8)	R _{0JC}	13.8	°C/W
Operating and Storage Temperature Range	T _J ,T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

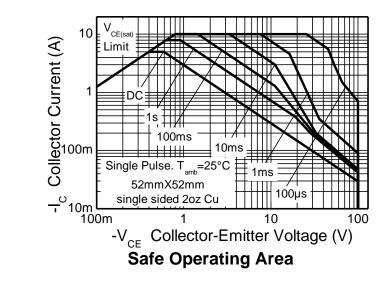
Notes:

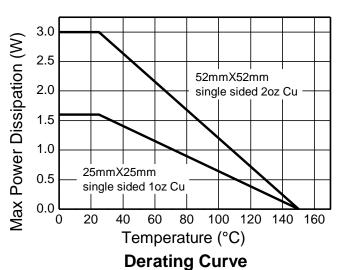
- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Thermal resistance from junction to top of the case.
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

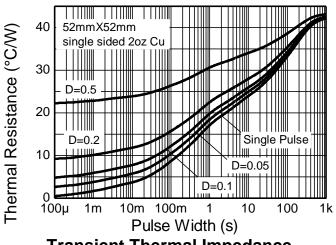


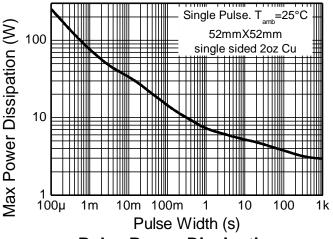


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation

May 2015

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Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-140	-160	_	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CER}	-140	-160	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-100	-115	_	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.1	_	V	I _E = -100μA
Collector Cut-Off Current	I _{CBO}	_ _	< 1 —	-20 -500	nA nA	V _{CB} = -100V V _{CB} = -100V, T _A = +100°C
Collector Cut-Off Current	I _{CER} R≤1kΩ	_ _	< 1 —	-20 -500	nA nA	V _{CB} = -100V V _{CB} = -100V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	_	< 1	-10	nA	V _{EB} = -6V
		100	250	_		$I_C = -10 \text{mA}, V_{CE} = -1 \text{V}$
		100	200	300		I _C = -1A, V _{CE} = -1V
DC Current Transfer Static Ratio (Note 10)	h _{FE}	25	50	_	_	I _C = -3A, V _{CE} = -1V
		15	30	_		I _C = -4A, V _{CE} = -1V
		_	5	_		$I_C = -10A$, $V_{CE} = -1V$
		_	-20	-30	mV	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Collector Emitter Coturation Voltage (Note 10)	M	_	-70	-90		$I_C = -1A$, $I_B = -100mA$
Collector-Emitter Saturation Voltage (Note 10)	VCE(SAT)	_	-120	-150		$I_C = -2A$, $I_B = -200mA$
		_	-240	-340		$I_C = -4A$, $I_B = -400mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(SAT)}	_	-985	-1,100	mV	$I_C = -4A$, $I_B = -400mA$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(ON)}	_	-920	-1,050	mV	$I_C = -4A$, $V_{CE} = -1V$
Transitional Frequency (Note 10)	f _T	_	125	_	MHz	I _C = -100mA, V _{CE} = -10V, f = 50MHz
Output Capacitance	C _{obo}	_	42	_	pF	V _{CB} = -10V, f = 1MHz
Switching Time	ton	_	42	_	no	$V_{CC} = -50V, I_{C} = -1A,$
Switching Time	toff	_	540	_	ns	$I_{B1} = -I_{B2} = -100 \text{mA}$

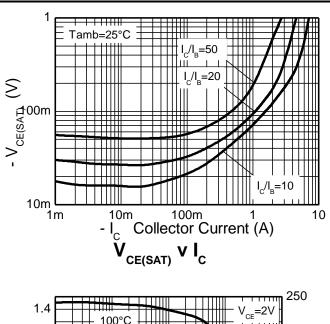
Note:

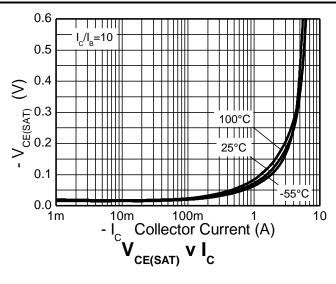
10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

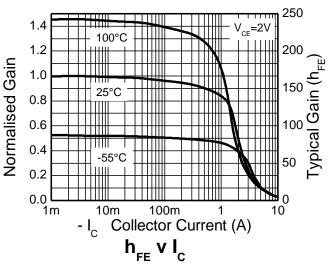


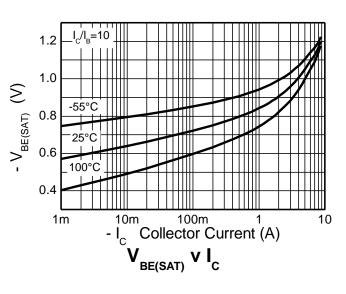


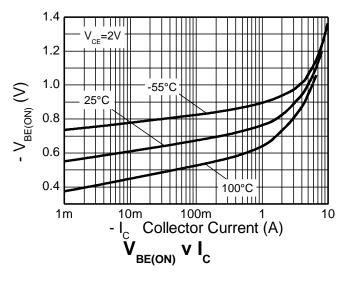
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







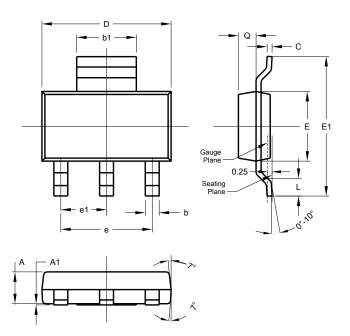






Package Outline Dimensions

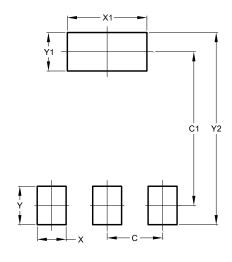
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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